



www.vishay.com

Vishay Semiconductors

AUTOMOTIVE GRADE

RoHS

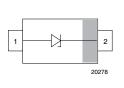
COMPLIANT

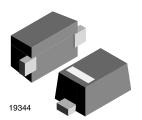
HALOGEN FREE

GREEN

(5-2008)

Single-Line ESD-Protection Diode in SOD-523





MARKING (example only)



Bar = cathode marking

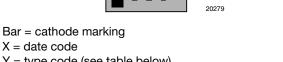
Y = type code (see table below)

LINKS TO ADDITIONAL RESOURCES



FEATURES

- Compact SOD-523 package
- Low package height < 0.7 mm
- 1-line unidirectional ESD-protection
- AEC-Q101 qualified available
- Working range 1 V to 33 V
- ESD immunity acc. IEC 61000-4-2 ±15 kV to ±30 kV contact discharge ±15 kV to ±30 kV air discharge
- Lead plating: Sn (e3)
 - soldering can be checked by standard vision inspection
 - AOI = automated optical inspection
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ORDERING II	NFORMAT	ION			
		ENVIRONMENTAL AND QUALITY CODE			
PART NUMBER (EXAMPLE)	AEC-Q101 QUALIFIED	RoHS COMPLIANT + LEAD (Pb)-FREE TERMINATIONS	TIN PLATED	8K PER 7" REEL (8 mm TAPE)	ORDERING CODE (EXAMPLE)
		GREEN		MOQ = 8K/BOX	
VESD05C1-02V	-	G	3	-08	VESD05C1-02V-G3-08
VESD05C1-02V	Н	G	3	-08	VESD05C1-02VHG3-08

PACKAGE DA	ATA														
DEVICE NAME	PACKAGE NAME	TYPE CODE	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS									
VESD01C1-02V		• A													
VESD03C1-02V		. 8	1.32 mg								<u> </u>				
VESD05C1-02V		. ၁													
VESD08C1-02V	SOD-523	. a		UL 94 V-0	ug UL 94 V-0	MSL level 1	Peak temperature max. 260 °C								
VESD12C1-02V	30D-323	-3	1.32 1119			(according J-STD-02	(according J-STD-020)	reak temperature max. 200 C							
VESD16C1-02V		. Đ													
VESD26C1-02V		К.													
VESD33C1-02V		Α													

Rev. 1.4, 15-Jan-2021 Document Number: 86130 For technical questions, contact: ESDprotection@vishay.com



VESD01C1-02V to VESD33C1-02V

Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS VESD01C1-02V (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	11	Α		
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	70	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	W	30	kV		
E3D IIIIIIIIIIIIII	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30	kV		
Operating temperature	Junction temperature	TJ	-55 to +150	°C		
Storage temperature		T _{stg}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS VESD03C1-02V (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	11.6	Α	
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	30	kV	
E3D IIIIIIuliity	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	30	kV	
Operating temperature	Junction temperature	TJ	-55 to +150	°C	
Storage temperature		T _{stg}	-55 to +150	°C	

ABSOLUTE MAXIMUM RATINGS VESD05C1-02V (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	8.7	Α	
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W	
ECD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	30	kV	
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	30	kV	
Operating temperature	Junction temperature	TJ	-55 to +150	°C	
Storage temperature		T _{stg}	-55 to +150	°C	

ABSOLUTE MAXIMUM RATINGS VESD08C1-02V (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	6.60	Α	
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W	
ECD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	30	kV	
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	30	kV	
Operating temperature	Junction temperature	TJ	-55 to +150	°C	
Storage temperature		T _{stg}	-55 to +150	°C	

Rev. 1.4, 15-Jan-2021 Document Number: 86130



VESD01C1-02V to VESD33C1-02V

Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS VESD12C1-02V (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	4.4	Α		
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P _{PP}	100	W		
CCD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	\/	30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	30	kV		
Operating temperature	Junction temperature	T _J	-55 to +150	°C		
Storage temperature		T _{sta}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS VESD16C1-02V (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	3.6	Α		
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W		
CCD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	30	kV		
Operating temperature	Junction temperature	TJ	-55 to +150	°C		
Storage temperature		T _{stg}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS VESD26C1-02V (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	2.1	Α		
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P _{PP}	100	W		
CCD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	\/	20	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	20	kV		
Operating temperature	Junction temperature	TJ	-55 to +150	°C		
Storage temperature		T _{stg}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS VESD33C1-02V (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	1.6	Α	
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P_PP	100	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	15	kV	
E3D IIIIIIIIIIIIII	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	15	kV	
Operating temperature	Junction temperature	T _J	-55 to +150	°C	
Storage temperature		T _{stg}	-55 to +150	°C	

Rev. 1.4, 15-Jan-2021 3 Document Number: 86130



VESD01C1-02V to VESD33C1-02V

Vishay Semiconductors

ELECTRICAL CHARACTERISTICS VESD01C1-02V (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	1	V
Reverse voltage	at I _R = 100 μA	V_R	1	1.2	-	V
Reverse current	at V _R = 1 V	I _R	-	20	100	μΑ
Deverse breekdown valtage	at I _R = 1 mA	V_{BR}	1.5	-	-	V
Reverse breakdown voltage	at I _R = 20 mA	V_{BR}	2.5	2.65	2.8	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 11 A, t _p = 8/20 μs	V _C	-	5.6	6.4	V
Converd elemping veltage	at I _{PP} = 1 A, t _p = 300 μs	V _F	0.9	1.1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 11 A, t _p = 8/20 μs	V _F	-	2.5	3.2	V
Dynamic resistance	t _p = 100 ns (TLP; pin 2-1)	r _{dyn}	-	0.13		Ω
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	153	192	230	pF

ELECTRICAL CHARACTERISTICS VESD03C1-02V (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	3	V
Reverse voltage	at I _R = 20 μA	V_R	3	-	-	V
Reverse current	at V _R = 3 V	I _R	-	8	20	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	4.4	4.65	4.9	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 11.6 \text{ A}, t_p = 8/20 \mu \text{s}$	V _C	-	7.8	8.70	V
Faruard alamaina valtaga	at I _{PP} = 1 A, t _p = 300 μs	V _F	0.9	1.1	1.2	V
Forward clamping voltage	at $I_{PP} = I_{PPM} = 11.6 \text{ A}, t_p = 8/20 \mu \text{s}$	V _F	-	2.6	3.32	V
Dynamic resistance	t _p = 100 ns (TLP; pin 2-1)	r _{dyn}	-	0.19	-	Ω
Capacitance	at V _R = 0 V; f = 1 MHz	C_{D}	89	112	135	pF

ELECTRICAL CHARAC (T _{amb} = 25 °C, unless oth	CTERISTICS VESD05C1-02V perwise specified)					
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	5	V
Reverse voltage	at I _R = 1 μA	V_R	5	-	-	V
Reverse current	at V _R = 5 V	I _R	-	0.01	0.1	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	6.85	7.26	7.65	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 8.7 \text{ A}$, $t_p = 8/20 \mu\text{s}$	V _C	-	10.3	11.5	V
Forward alamaina valtaga	at I _{PP} = 1 A, t _p = 300 μs	V _F	0.9	1.1	1.2	V
Forward clamping voltage	at $I_{PP} = I_{PPM} = 8.7 \text{ A}$, $t_p = 8/20 \mu\text{s}$	V_{F}	-	2.2	2.74	V
Dynamic resistance	t _p = 100 ns (TLP; pin 2-1)	r _{dyn}	-	0.2	-	Ω
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	53	67	81	pF

Rev. 1.4, 15-Jan-2021 **4** Document Number: 86130



Forward clamping voltage

Dynamic resistance

Capacitance

VESD01C1-02V to VESD33C1-02V

Vishay Semiconductors

1.2

2.32

٧

٧

Ω

рF

ELECTRICAL CHARAC (T _{amb} = 25 °C, unless oth	CTERISTICS VESD08C1-02V erwise specified)					
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	8	V
Reverse voltage	at I _R = 0.1 μA	V_R	8	-	-	V
Reverse current	at V _R = 8 V	I _R	-	0.01	0.1	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	9.5	10	10.5	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 6.6 A, t _p = 8/20 μs	V _C	-	13.7	15.3	V

 V_{F}

 V_{F}

 r_{dyn}

 C_{D}

0.9

37

1.1

1.9

0.23

47

at $I_{PP} = 1 \text{ A}$, $t_p = 300 \ \mu s$

at $I_{PP} = I_{PPM} = 6.6 \text{ A}, t_p = 8/20 \ \mu s$

 $t_p = 100 \text{ ns (TLP; pin 2-1)}$

at $V_R = 0 V$; f = 1 MHz

ELECTRICAL CHARAC (T _{amb} = 25 °C, unless oth	CTERISTICS VESD12C1-02V nerwise specified)					
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	12	V
Reverse voltage	at I _R = 0.1 μA	V_R	12	-	-	V
Reverse current	at V _R = 12 V	I _R	-	0.01	0.1	μA
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	13.9	14.7	15.5	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 4.4 \text{ A}$, $t_p = 8/20 \mu\text{s}$	V _C	-	20.5	22.7	V
Converd elemning veltage	at I _{PP} = 1 A, t _p = 300 μs	V_{F}	0.9	1.1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 4.4 A, t _p = 8/20 μs	V_{F}	-	1.6	1.88	V
Dynamic resistance	t _p = 100 ns (TLP; pin 2-1)	r _{dyn}	-	0.4	-	Ω
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	26	33	40	pF

ELECTRICAL CHARAC (T _{amb} = 25 °C, unless oth	CTERISTICS VESD16C1-02V nerwise specified)					
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	ı	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	16	V
Reverse voltage	at I _R = 0.1 μA	V_R	16	-	-	V
Reverse current	at V _R = 16 V	I _R	-	0.01	0.1	μA
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	17	17.9	18.8	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 3.6 \text{ A}, t_p = 8/20 \mu\text{s}$	V _C	-	25.3	28	V
Converd elemning veltage	at I _{PP} = 1 A, t _p = 300 μs	V_{F}	0.9	1.1	1.2	V
Forward clamping voltage	at $I_{PP} = I_{PPM} = 3.6 \text{ A}, t_p = 8/20 \mu \text{s}$	V_{F}	-	1.5	1.72	V
Dynamic resistance	t _p = 100 ns (TLP; pin 2-1)	r _{dyn}	-	0.53	-	Ω
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	21	27	33	pF

Rev. 1.4, 15-Jan-2021 5 Document Number: 86130



Dynamic resistance

Capacitance

VESD01C1-02V to VESD33C1-02V

Vishay Semiconductors

1.42

21

1.3

1.9

17.5

٧

Ω

рF

ELECTRICAL CHARAC (T _{amb} = 25 °C, unless oth	CTERISTICS VESD26C1-02V erwise specified)					
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	26	V
Reverse voltage	at I _R = 0.1 μA	V_R	26	-	-	V
Reverse current	at V _R = 26 V	I _R	-	< 0.01	0.1	μA
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	27.6	29.1	30.6	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 2.1 \text{ A}, t_p = 8/20 \mu \text{s}$	V _C	-	43	48	V
Forward clamping voltage	at I _{PP} = 1 A, t _p = 300 μs	V _F	0.9	1.1	1.2	V
	at 1 01 A + 0/00	\/		1.0	1 40	W

 V_{F}

 r_{dyn}

 C_{D}

14

at $I_{PP} = I_{PPM} = 2.1 \text{ A}, t_p = 8/20 \mu s$

 $t_p = 100 \text{ ns (TLP; pin 2-1)}$

at $V_R = 0 V$; f = 1 MHz

ELECTRICAL CHARAC (T _{amb} = 25 °C, unless oth	CTERISTICS VESD33C1-02V perwise specified)					
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	33	V
Reverse voltage	at I _R = 0.1 μA	V_R	33	-	-	V
Reverse current	at V _R = 33 V	I _R	-	< 0.01	0.1	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	35.5	37.4	39.3	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 1.6 A, t _p = 8/20 μs	V _C	-	56	62.5	V
Famus val alamania a valla ara	at I _{PP} = 1 A, t _p = 300 μs	V_{F}	0.9	1.1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 1.6 A, t _p = 8/20 μs	V_{F}	-	1.22	1.32	V
Dynamic resistance	t _p = 100 ns (TLP; pin 2-1)	r _{dyn}	-	3.6	-	Ω
Capacitance	at V _R = 0 V; f = 1 MHz	C_D	12	15	18	pF

Rev. 1.4, 15-Jan-2021 Document Number: 86130

Vishay Semiconductors

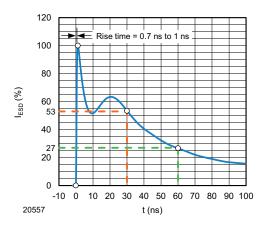


Fig. 1 - ESD Discharge Current Wave Form acc. IEC 61000-4-2 (330 Ω / 150 pF)

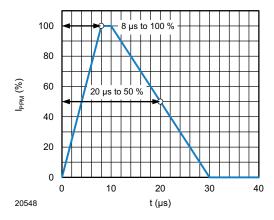


Fig. 2 - 8/20 µs Peak Pulse Current Wave Form acc. IEC 61000-4-5

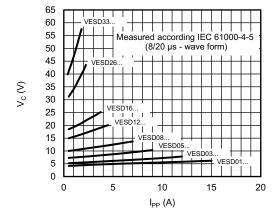


Fig. 3 - Typical Peak Clamping Voltage vs. Peak Pulse Current

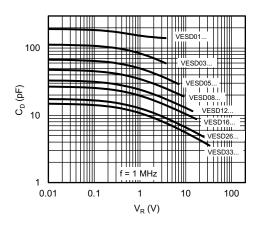


Fig. 4 - Typical Capacitance vs. Reverse Voltage

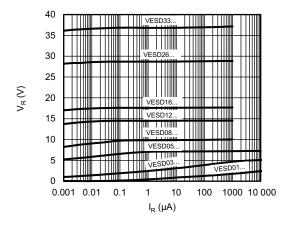


Fig. 5 - Typical Reverse Voltage vs. Reverse Current

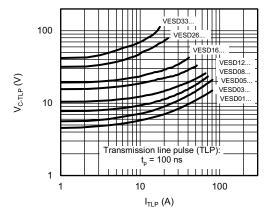


Fig. 6 - Typical Clamping Voltage vs. Peak Pulse Current

Rev. 1.4, 15-Jan-2021 7 Document Number: 86130





Vishay Semiconductors

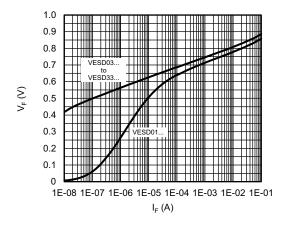


Fig. 7 - Typical Forward Voltage vs. Forward Current

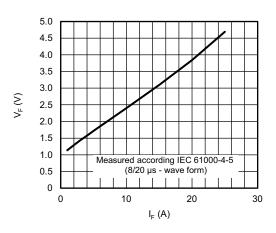
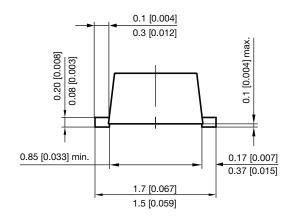
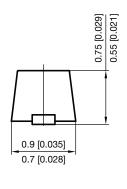


Fig. 8 - Typical Forward Voltage vs. Forward Current

PACKAGE DIMENSIONS in millimeters [inches]: SOD-523

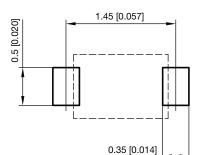




1.3 [0.051] 1.1 [0.043]

Document no.: S8-V-3880.02-003 (4) Created - Date: 04. April 2017 Rev. 4 - Date: 03. Aug. 2020

23093



Footprint recommendation:

Rev. 1.4, 15-Jan-2021 8 Document Number: 86130

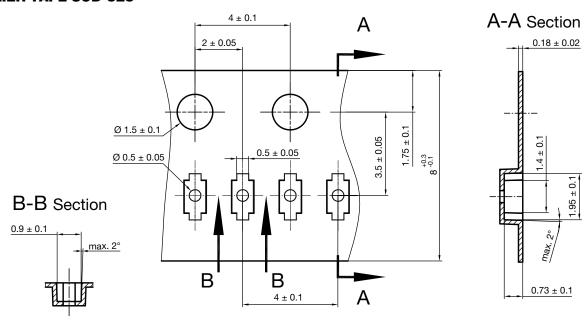




www.vishay.com

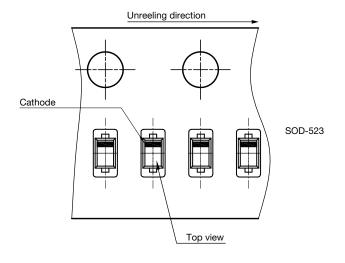
Vishay Semiconductors

CARRIER TAPE SOD-523



S8-V-3717.03-005 (4) 05.07.2018 22959

ORIENTATION IN CARRIER TAPE SOD-523



S8-V-3717.03-006 (4) 05.07.2018 22958

Rev. 1.4, 15-Jan-2021 9 Document Number: 86130

Legal Disclaimer Notice



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2022 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED